

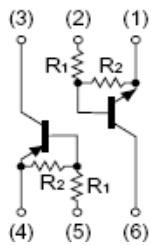
dual digital transistors (NPN+PNP)

FEATURES

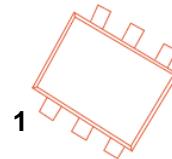
Two DTA114Y and DTC114Y transistors are built-in a package

Marking: D9

Equivalent circuit



SOT-563



DTr1 Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Supply voltage	V_{CC}	50	V
Input voltage	V_{IN}	-6~+40	V
Output current	I_O	70	mA
	$I_{C(MAX)}$	100	
Power dissipation	P_d	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~150	°C

Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Input voltage	$V_{I(off)}$			0.3	V	$V_{CC}=5V, I_O=100\mu\text{A}$
	$V_{I(on)}$	1.4				$V_o=0.3V, I_O=1\text{mA}$
Output voltage	$V_{O(on)}$		0.1	0.3	V	$I_O=5\text{mA}, I_I=0.25\text{mA}$
Input current	I_I			0.88	mA	$V_i=5V$
Output current	$I_{O(off)}$			0.5	μA	$V_{CC}=50V, V_i=0$
DC current gain	G_I	68				$V_o=5V, I_O=5\text{mA}$
Input resistance	R_I	7	10	13	KΩ	
Resistance ratio	R_2/R_1	3.7	4.7	5.7		
Transition frequency	f_T		250		MHz	$V_o=10V, I_O=5\text{mA}, f=100\text{MHz}$

DTr2 Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Supply voltage	V_{CC}	-50	V
Input voltage	V_{IN}	-40~+6	V
Output current	I_O	-70	mA
	$I_{O(MAX)}$	-100	
Power dissipation	P_d	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55~150	$^\circ\text{C}$

Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Input voltage	$V_{I(off)}$			-0.3	V	$V_{CC}=-5\text{V}, I_O=-100\mu\text{A}$
	$V_{I(on)}$	-1.4				$V_O=-0.3\text{V}, I_O=-1\text{mA}$
Output voltage	$V_{O(on)}$		-0.1	-0.3	V	$I_O=-5\text{mA}, I_I=-0.25\text{mA}$
Input current	I_I			-0.88	mA	$V_I=-5\text{V}$
Output current	$I_{O(off)}$			-0.5	μA	$V_{CC}=-50\text{V}, V_I=0$
DC current gain	G_I	68				$V_O=-5\text{V}, I_O=-5\text{mA}$
Input resistance	R_I	7	10	13	$\text{K}\Omega$	
Resistance ratio	R_2/R_1	3.7	4.7	5.7		
Transition frequency	f_T		250		MHz	$V_O=-10\text{V}, I_O=-5\text{mA}, f=100\text{MHz}$